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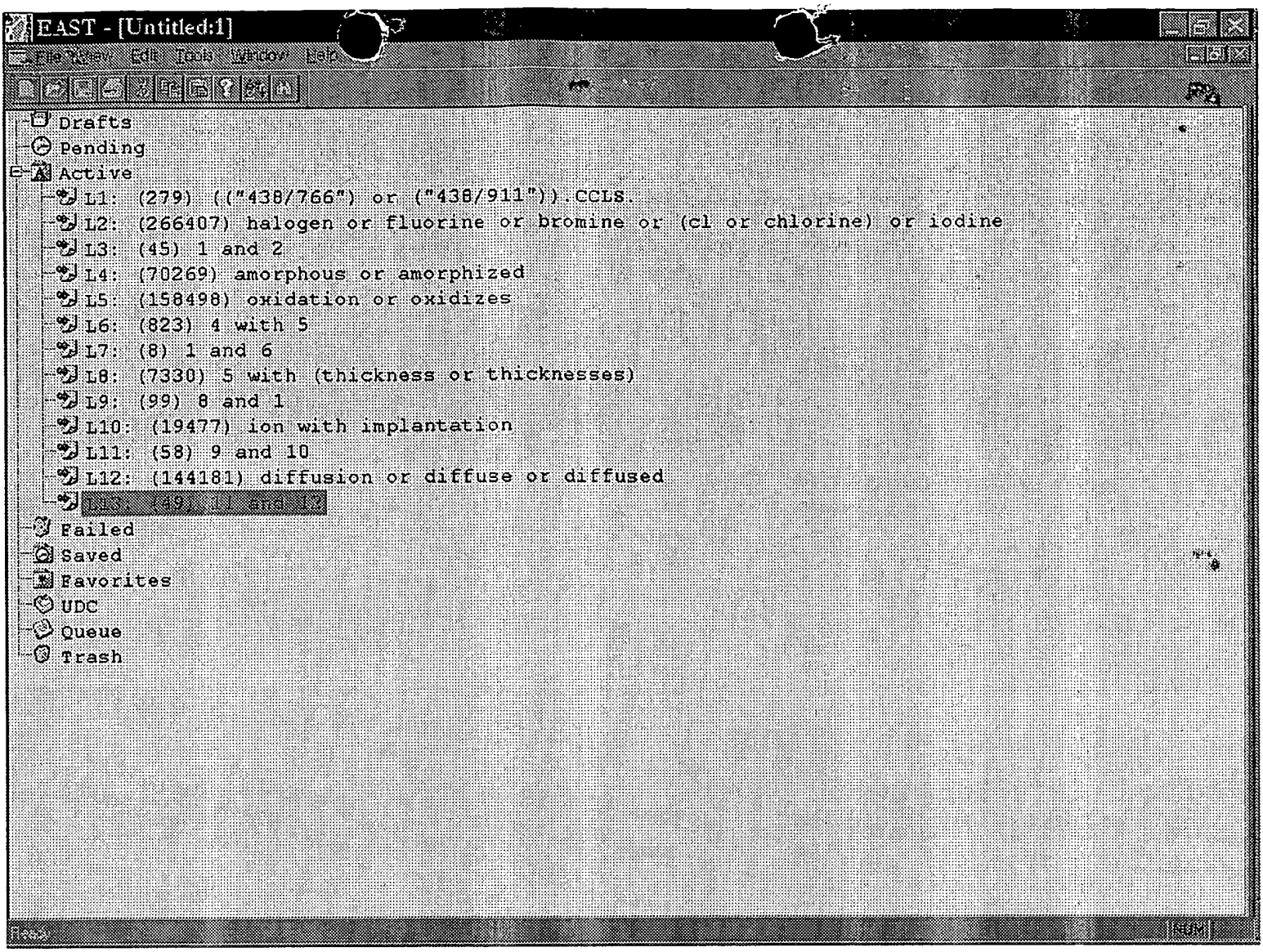
3	L3	25	1 and 2	USPAT


EAST - [Untitled:1]
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Drafts
Pending
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L1: (279) (("438/766") or ("438/911")).CCLS.
L2: (266407) halogen or fluorine or bromine or (cl or chlorine) or iodine
L3: (45) 1 and 2
L4: (70269) amorphous or amorphized
L5: (158498) oxidation or oxidizes
L6: (823) 4 with 5
L7: (8) 1 and 6
L8: (7330) 5 with (thickness or thicknesses)
L9: (99) 8 and 1
L10: (19477) ion with implantation
L11: (58) 9 and 10
L12: (144181) diffusion or diffuse or diffused
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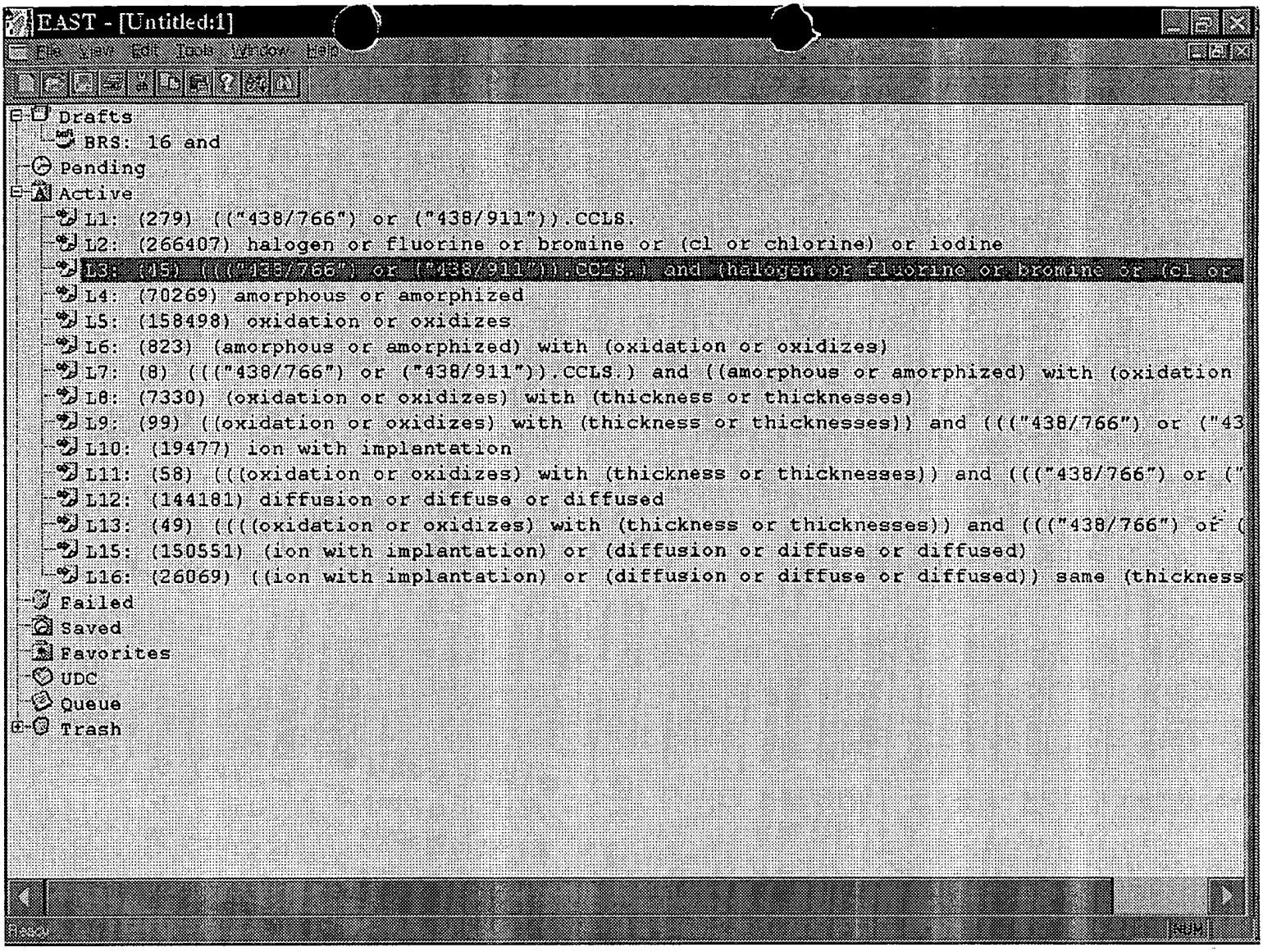
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Drafts
BRS: 16 and
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L1: (279) (("438/766") or ("438/911")).CCLS.
L2: (266407) halogen or fluorine or bromine or (cl or chlorine) or iodine
L3: (15) ((("438/766") or ("438/911")).CCLS.) and (halogen or fluorine or bromine or (cl or
L4: (70269) amorphous or amorphized
L5: (158498) oxidation or oxidizes
L6: (823) (amorphous or amorphized) with (oxidation or oxidizes)
L7: (8) ((("438/766") or ("438/911")).CCLS.) and ((amorphous or amorphized) with (oxidation
L8: (7330) (oxidation or oxidizes) with (thickness or thicknesses)
L9: (99) ((oxidation or oxidizes) with (thickness or thicknesses)) and ((("438/766") or ("43
L10: (19477) ion with implantation
L11: (58) (((oxidation or oxidizes) with (thickness or thicknesses)) and ((("438/766") or ("
L12: (144181) diffusion or diffuse or diffused
L13: (49) ((((oxidation or oxidizes) with (thickness or thicknesses)) and ((("438/766") or (
L15: (150551) (ion with implantation) or (diffusion or diffuse or diffused)
L16: (26069) ((ion with implantation) or (diffusion or diffuse or diffused)) same (thickness
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	Type	L #	Hits	Search Text
1	IS&R	L1	279	(("438/766") or ("438/911")).CCLS.
2	BRS	L2	266407	halogen or fluorine or bromine or (cl or chlorine) or iodine
3	BRS	L3	45	1 and 2
4	BRS	L4	70269	amorphous or amorphized
5	BRS	L5	158498	oxidation or oxidizes
6	BRS	L6	823	4 with 5
7	BRS	L7	8	1 and 6
8	BRS	L8	7330	5 with (thickness or thicknesses)
9	BRS	L9	99	8 and 1
10	BRS	L10	19477	ion with implantation
11	BRS	L11	58	9 and 10
12	BRS	L12	144181	diffusion or diffuse or diffused
13	BRS	L13	49	11 and 12

	Type	L #	Hits	Search Text
1	IS&R		279	(("438/766") or ("438/911")).CCLS.
2	BRS		266407	halogen or fluorine or bromine or (cl or chlorine) or iodine
3	BRS		45	((("438/766") or ("438/911")).CCLS.) and (halogen or fluorine or bromine or (cl or chlorine) or iodine)
4	BRS		70269	amorphous or amorphized
5	BRS		158498	oxidation or oxidizes
6	BRS		823	(amorphous or amorphized) with (oxidation or oxidizes)
7	BRS		8	((("438/766") or ("438/911")).CCLS.) and ((amorphous or amorphized) with (oxidation or oxidizes))
8	BRS		7330	(oxidation or oxidizes) with (thickness or thicknesses)
9	BRS		99	((oxidation or oxidizes) with (thickness or thicknesses)) and ((("438/766") or ("438/911")).CCLS.)
10	BRS		19477	ion with implantation
11	BRS		58	(((oxidation or oxidizes) with (thickness or thicknesses)) and ((("438/766") or ("438/911")).CCLS.)) and (ion with implantation)
12	BRS		144181	diffusion or diffuse or diffused
13	BRS		49	((((oxidation or oxidizes) with (thickness or thicknesses)) and ((("438/766") or ("438/911")).CCLS.)) and (ion with implantation)) and (diffusion or diffuse or diffused)
14	BRS		150551	(ion with implantation) or (diffusion or diffuse or diffused)

	Type	L #	Hits	Search Text
15	BRS		26069	((ion with implantation) or (diffusion or diffuse or diffused)) same (thickness or thicknesses)

	Type	L #	Hits	Search Text	DBs
1	IS&R	L1	279	(("438/766") or ("438/911")).CCLS.	USPAT
2	BRS	L2	266407	halogen or fluorine or bromine or (cl or chlorine) or iodine	USPAT
3	BRS	L3	45	1 and 2	USPAT
4	BRS	L4	70269	amorphous or amorphized	USPAT
5	BRS	L5	158498	oxidation or oxidizes	USPAT
6	BRS	L6	823	4 with 5	USPAT
7	BRS	L7	8	1 and 6	USPAT

1 and 5

221589

8 1 and 5

9 thickness or thicknesses

10

8 5 with (thickness or thicknesses)

9 8 and 1

look at text for highlighted terms

	Type	L #	Hits	Search Text
1	IS&R		440	(("438/766") or ("438/770") or ("438/911")).CCLS.
2	BRS		266407	halogen or fluorine or bromine or iodine or (chlorine or Cl)
3	BRS		135	differential adj oxidation
4	BRS		266527	(halogen or fluorine or bromine or iodine or (chlorine or Cl)) ~~or~~ and (differential adj oxidation)
5	BRS		78	((("438/766") or ("438/770") or ("438/911")).CCLS.) and (halogen or fluorine or bromine or iodine or (chlorine or Cl))
6	BRS		82	((("438/766") or ("438/770") or ("438/911")).CCLS.) and ((halogen or fluorine or bromine or iodine or (chlorine or Cl)) or (differential adj oxidation))
7	BRS	L49	4	((("438/766") or ("438/770") or ("438/911")).CCLS.) and (differential adj oxidation)
8	BRS	L50	0	4 and 6
9	BRS	L51	174	438/766
10	BRS	L52	0	51 and 3

halogen <and> oxidation Refine

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FILE COVERS 1969 TO DATE.

=> **halogen**
L1 5581 HALOGEN

=> e oxidation +all/ct
E1 12179 BT1 CHEMICAL REACTIONS/CT
E2 32602 --> OXIDATION/CT
DA JANUARY 1969
E3 0 UF RAPID THERMAL OXIDATION/CT
E4 6983 NT1 COMBUSTION/CT
E5 1370 NT2 COMBUSTION SYNTHESIS/CT
E6 2588 RT ANODISATION/CT
E7 16190 RT CORROSION/CT

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E8        3581      RT   ENVIRONMENTAL DEGRADATION/CT
E9        1082      RT   ISOLATION TECHNOLOGY/CT
E10       1859      RT   NITRIDATION/CT
E11       8850      RT   PASSIVATION/CT
E12       2009      RT   RAPID THERMAL PROCESSING/CT
E13       5226      RT   REDUCTION (CHEMICAL)/CT
E14      14160      RT   SEMICONDUCTOR TECHNOLOGY/CT
E15      16465      RT   SURFACE CHEMISTRY/CT
E16      12382      RT   SURFACE TREATMENT/CT
E17      14050      CC   A8160/CT
E18       9435      CC   A8230/CT
E19      32577      CC   B2550E/CT
E20          0      KT   ANODIC OXIDATION/CT
E21          0      KT   RAPID THERMAL OXIDATION/CT
*********  END  *********

=> e gate +all/ct
E1           0   -->  GATE/CT
E2        3295    KT   FIELD PROGRAMMABLE GATE ARRAYS/CT
E3           0    KT   GATE ARRAYS/CT
E4           0    KT   GATE TURN-OFF DEVICES/CT
E5        2603    KT   INSULATED GATE BIPOLAR TRANSISTORS/CT
E6       10946    KT   INSULATED GATE FIELD EFFECT TRANSISTORS/CT
E7        1199    KT   JUNCTION GATE FIELD EFFECT TRANSISTORS/CT
E8        5382    KT   SCHOTTKY GATE FIELD EFFECT TRANSISTORS/CT
*********  END  *********

=> e6
L2       10946 "INSULATED GATE FIELD EFFECT TRANSISTORS"/CT  (3 TERMS)

=> d his

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     FILE 'INSPEC' ENTERED AT 18:46:14 ON 30 AUG 2000
L1         5581 HALOGEN
                E OXIDATION +ALL/CT
                E GATE +ALL/CT
L2        10946 E6

=> l1 and l2
L3           5 L1 AND L2

=> d 1-5 ab

L3   ANSWER 1 OF 5  INSPEC  COPYRIGHT 2000 IEE
AB   Metal-oxide-semiconductor field effect transistors (MOSFETs), fabricated
     in a simple Al gate process, have been subjected to rapid thermal
     annealing cycles of four different types immediately following the gate
     oxide growth. Fundamental MOS interface properties have been determined
     and compared as a function of the annealing temperature Tan. The influence
     of the steady state time tan at high temperature has been studied for a
     standard cycle; no effect was found for Tan=1200 degrees C and
     3shalogen lamps, have been carried out to achieve
good contact areas at low depth (0;1 mu m) as well as n-type channels of
MIS transistors. The crystallographic disorder remaining after annealing
and its influence on the carrier distribution are discussed. The
uniformity of activation has been evaluated by wafer scanning of Hall
effect and specific contact resistivity. Finally, characteristics of MIS
transistors are given.

L3  ANSWER 3 OF 5  INSPEC  COPYRIGHT 2000 IEE
AB  A chemical vapor deposition reactor has been designed with tungsten
    halogen lamps as a source of radiant heat. This rapid thermal CVD system
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can be used to fabricate thin layers of semiconductors, metals and insulators by a precise control of thermally driven surface reactions. Radiant heat is used to produce large, yet rapid changes in the temperature of the semiconductor substrate. From a mixture of silane and oxygen gas SiO2 layers have been fabricated at 700 degrees C. At this elevated temperature deposition rates of 100 AA/sec are obtained. These layers could be deposited on InP substrate with resulting specular surfaces. Optical as well as electrical characterization of these films indicates that the structure is perfectly suited for InP MIS-FET applications.

L3 ANSWER 4 OF 5 INSPEC COPYRIGHT 2000 IEE
AB Rapid thermal processing with **halogen** lamp heating is found to be effective in forming oxide-free titanium silicide. The silicidation reaction is completed within as short a time as 30 sec, and yields stoichiometric titanium disilicide with a resistivity of 14-16 mu ohm-cm. A self-aligned silicidation achieved by oxide side walls combined with a LDD structure produces submicron MOS transistors with 2-3 ohm/sq of sheet resistance of source/drain and gate. The gate dielectric integrity and the junction integrity of silicided devices are comparable with those of control devices without silicidation.

L3 ANSWER 5 OF 5 INSPEC COPYRIGHT 2000 IEE
AB The unit described was designed with BUZ 4. SIPMOS transistors to supply low-voltage **halogen** lamps and uses a self-exciting half-bridge circuit. The circuits were designed for **halogen** lamps operating at 24 V/250 W, 24 V/150 W and 12 V/50 W. At rated duty the working frequency is approximately 120 kHz. This high frequency was chosen to keep the winding dimensions as small as possible and also to keep the RFI suppression requirements to a minimum. Efficiency achieved, depending on the power of the lamp, is between 85 and 90%. Weight is reduced to between one tenth and one fifteenth of that of a 50-Hz transformer.

=> **d his**

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L1 5581 HALOGEN
E OXIDATION +ALL/CT
E GATE +ALL/CT
L2 10946 E6
L3 5 L1 AND L2

=>